

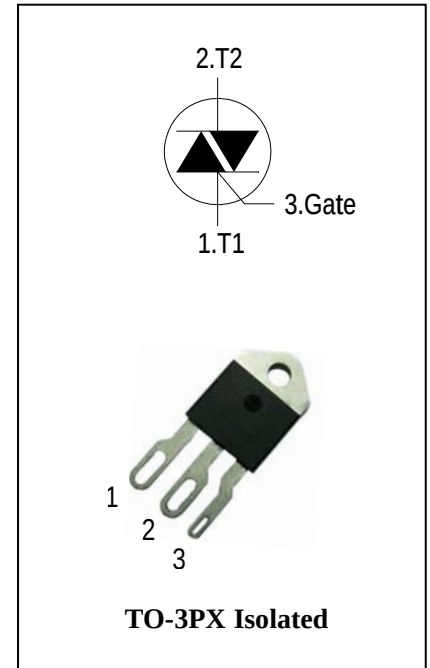
### 3 Quadrants Triacs

#### General Description

High current density due to mesa technology .the AIS40C triac series is suitable for general purpose AC switching. They can be used as an ON/OFF function in applications such as static relays, heating regulation, High power motor controls e.g. washing machines and vacuum cleaners, Rectifier-fed DC inductive loads e.g. DC motors and solenoids , motor speed controllers.

#### Features

- ◆ Repetitive Peak Off-State Voltage: 600V and 800V
- ◆ R.M.S On-State Current (  $I_{T(RMS)} = 40A$  )
- ◆ High Commutation  $dv/dt$
- ◆ These Devices are Pb-Free and are RoHS Compliant
- ◆ Isolated heatsink mounted , Isolation Voltage (  $V_{ISO} = 2500V AC$  )



#### Absolute Maximum Ratings

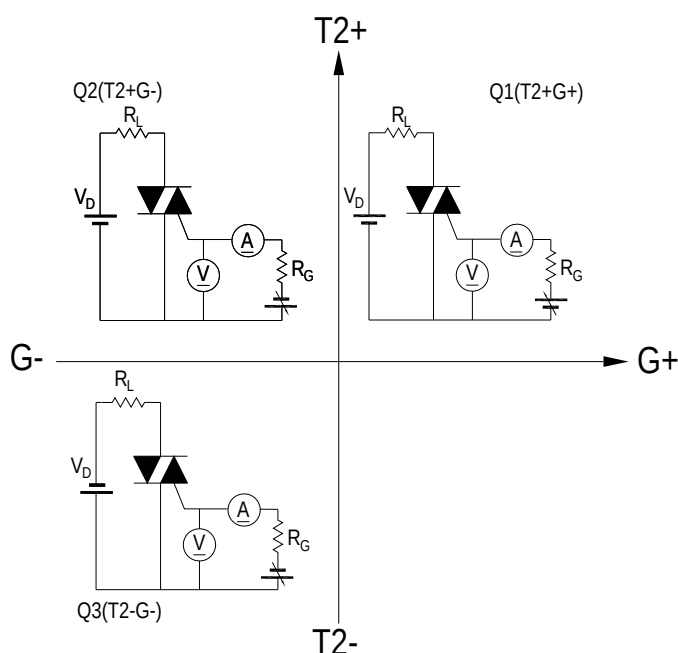
| Symbol                 | Items                                                          | Conditions                                                                                    |           | Ratings    | Unit        |
|------------------------|----------------------------------------------------------------|-----------------------------------------------------------------------------------------------|-----------|------------|-------------|
| $V_{DRM}$<br>$V_{RRM}$ | Repetitive Peak Off-State Voltage                              | $T_j = 25^{\circ}C$                                                                           | AIS40C60X | 600        | V           |
|                        |                                                                |                                                                                               | AIS40C80X | 800        | V           |
| $I_{T(RMS)}$           | R.M.S On-State Current                                         | $T_C = 80^{\circ}C$                                                                           |           | 40         | A           |
| $I_{TSM}$              | Surge On-State Current                                         | $t_p=20ms(50Hz)/t_p=16.7ms(60Hz)$                                                             |           | 400/420    | A           |
| $I^2t$                 | $I^2t$ for fusing                                              | $t_p=10ms$                                                                                    |           | 880        | $A^2s$      |
| $di/dt$                | Critical rate of rise of on-state current                      | $F = 120\text{ Hz}$ $T_j = 125^{\circ}C$<br>$I_G = 2 \times I_{GT}$ , $tr \leq 100\text{ ns}$ |           | 50         | $A/\mu s$   |
| $I_{GM}$               | Peak Gate Current                                              | $t_p = 20\text{ }\mu s$ $T_j = 125^{\circ}C$                                                  |           | 8          | A           |
| $P_{G(AV)}$            | Average Gate Power Dissipation( $T_j=125^{\circ}C$ )           |                                                                                               |           | 1          | W           |
| $P_{GM}$               | Peak Gate Power Dissipation( $t_p=20\mu s, T_j=125^{\circ}C$ ) |                                                                                               |           | 10         | W           |
| $T_j$                  | Operating Junction Temperature                                 |                                                                                               |           | - 40 ~ 125 | $^{\circ}C$ |
| $T_{STG}$              | Storage Temperature                                            |                                                                                               |           | - 40 ~ 150 | $^{\circ}C$ |



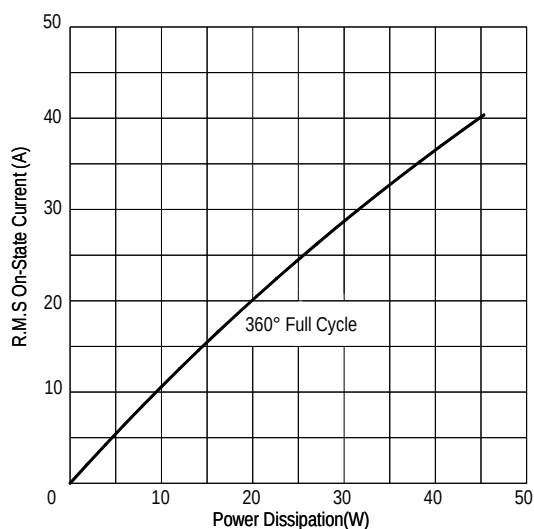
## Electrical Characteristics( $T_j = 25^\circ\text{C}$ unless otherwise specified )

| Symbol                               | Items                                          |                          | Conditions                                                                                                       |      | AIS40C60XB/80XB | Unit |
|--------------------------------------|------------------------------------------------|--------------------------|------------------------------------------------------------------------------------------------------------------|------|-----------------|------|
| $I_{\text{DRM}}$<br>$I_{\text{RRM}}$ | Peak Forward Reverse Blocking Current          |                          | $V_{\text{DRM}} = V_{\text{RRM}}, T_{\text{j}} = 25^{\circ}\text{C}$                                             | Max. | 5               | uA   |
|                                      |                                                |                          | $V_{\text{DRM}} = V_{\text{RRM}}, T_{\text{j}} = 125^{\circ}\text{C}$                                            |      | 5               | mA   |
| $V_{\text{TM}}$                      | Peak On-State Voltage                          |                          | $I_{\text{TM}} = 60\text{A}, t_{\text{p}} = 380 \mu\text{s}$                                                     | Max. | 1.55            | V    |
| $V_{\text{GD}}$                      | Q1-Q2-Q3                                       | Non—Trigger Gate Voltage | $V_{\text{D}} = V_{\text{DRM}} \quad R_{\text{L}} = 3.3 \text{ k}\Omega$<br>$T_{\text{j}} = 125^{\circ}\text{C}$ | Min. | 0.2             | V    |
| $V_{\text{GT}}$                      | Q1-Q2-Q3                                       | Gate Trigger Voltage     | $V_{\text{D}} = 12\text{V} \quad , \quad R_{\text{L}} = 33\Omega$                                                | Max. | 1.3             | V    |
| $I_{\text{GT}}$                      | Q1-Q2-Q3                                       | Gate Trigger Current     |                                                                                                                  | Max. | 50              | mA   |
| $I_{\text{H}}$                       | Q1-Q2-Q3                                       | Holding Current          | $I_{\text{T}} = 0.5\text{A}$                                                                                     | Max. | 75              | mA   |
| $I_{\text{L}}$                       | Q1-Q3                                          | Latching Current         | $I_{\text{G}} = 1.2 I_{\text{GT}}$                                                                               | Max. | 90              | mA   |
|                                      | Q2                                             |                          |                                                                                                                  |      | 110             |      |
| dV/dt                                | Critical Rate of Rise of Off-State Voltage     |                          | $V_{\text{D}} = 2/3V_{\text{DRM}} \quad \text{gate open}$<br>$T_{\text{j}} = 125^{\circ}\text{C}$                | Min. | 1500            | V/μs |
| (dV/dt)c                             | Critical Rate of Change of Commutating Voltage |                          | (dI/dt)c=-20A/ms<br>$T_{\text{j}} = 125^{\circ}\text{C}$                                                         | Min. | 20              | V/μs |
| $R_{\text{th(j-c)}}$                 | Junction to case (AC)                          |                          |                                                                                                                  | Max. | 0.9             | °C/W |
| $R_{\text{th(j-a)}}$                 | Junction to ambient                            |                          |                                                                                                                  | Max. | 50              | °C/W |

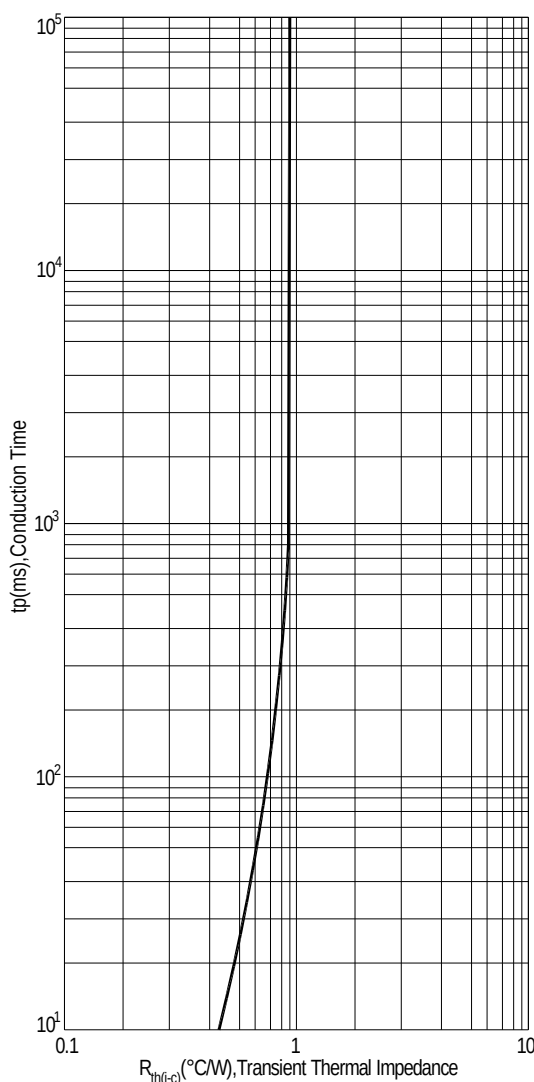
FIG.1: Triac quadrant are defined and the gate trigger test circuit



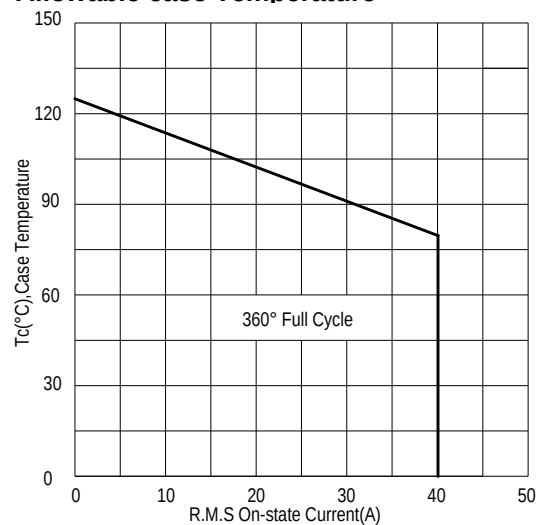
**FIG.2: Maximum on-state power dissipation**



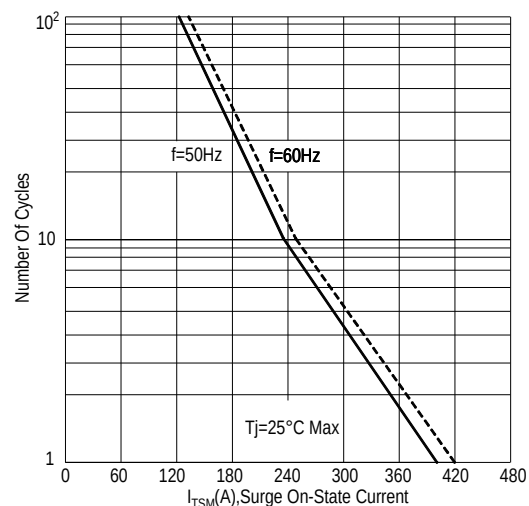
**FIG.4: Maximum transient thermal impedance**



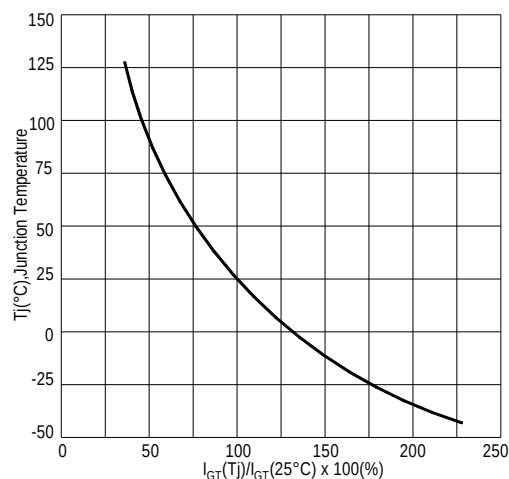
**FIG.3: Typical RMS on-state current VS Allowable case Temperature**



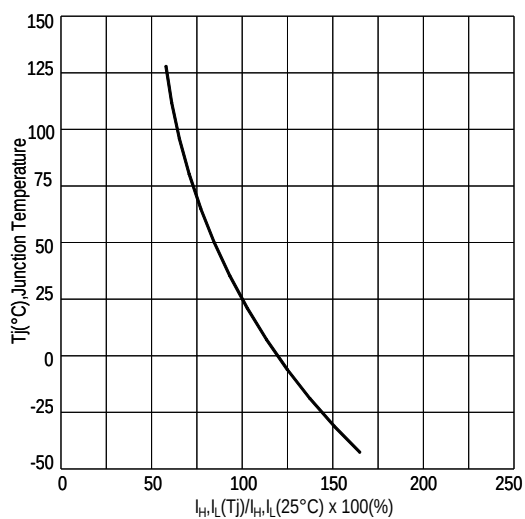
**FIG.5: Rated surge on-state current ( Non-Repetitive)**



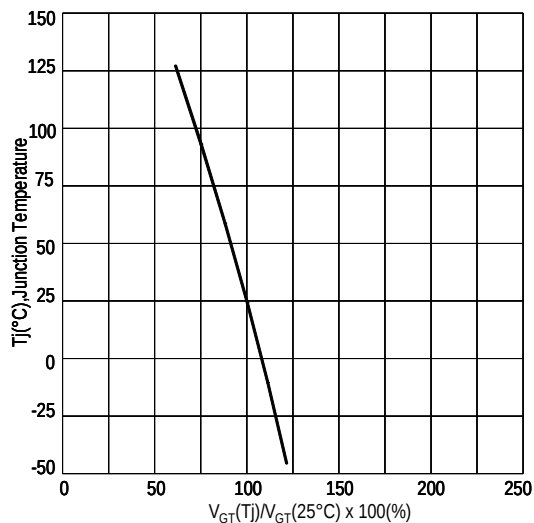
**FIG.6: Gate trigger current VS Junction temperature**



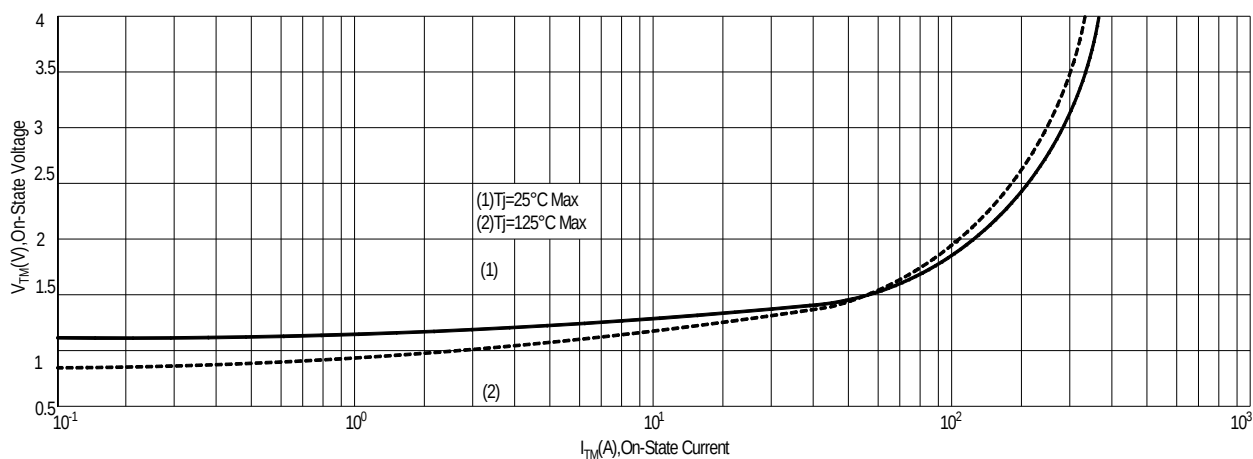
**FIG.7: Holding current and Latching current VS Junction temperature**



**FIG.8: Gate trigger voltage VS Junction temperature**

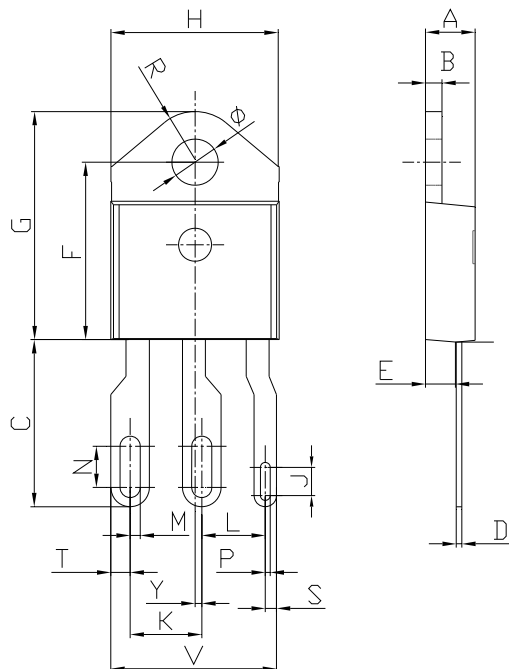


**FIG.9: On-state characteristics(Max)**



## PACKAGE MECHANICAL DATA

### TO-3PX(isolated) Package Dimension



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 4.40                      | 4.60  | 0.173                | 0.181 |
| B      | 1.45                      | 1.55  | 0.057                | 0.061 |
| C      | 14.35                     | 15.60 | 0.565                | 0.614 |
| D      | 0.50                      | 0.70  | 0.020                | 0.028 |
| E      | 2.70                      | 2.90  | 0.106                | 0.114 |
| F      | 15.80                     | 16.50 | 0.622                | 0.650 |
| G      | 20.40                     | 21.10 | 0.815                | 0.831 |
| H      | 15.10                     | 15.50 | 0.594                | 0.610 |
| J      | 2.87                      | 3.07  | 0.113                | 0.121 |
| K      | 6.50                      | 6.71  | 0.256                | 0.264 |
| Ø      | 4.08                      | 4.20  | 0.161                | 0.165 |
| L      | 5.58                      | 5.79  | 0.220                | 0.228 |
| P      | 0.43                      | 0.53  | 0.017                | 0.020 |
| N      | 4.29                      | 4.49  | 0.169                | 0.177 |
| M      | 1.015                     | 1.12  | 0.040                | 0.044 |
| T      | 1.98                      | 2.11  | 0.078                | 0.083 |
| Y      | 0.71                      | 0.81  | 0.028                | 0.032 |
| V      | 15.31                     | 15.70 | 0.603                | 0.618 |
| S      | 1.09                      | 1.22  | 0.086                | 0.096 |
| R      | 4.60 typ.                 |       | 0.181 typ.           |       |

## Making Diagram

ADV:Logo  
AIS40C60XB:Part number  
X:Internal control code  
H:Halogen Free

**A I S 40 C 60 X B**

ADVANCED  
isolated  
Internal control code  
Current:40=40A  
Quadrant:C=3Q

Sensitivity and type:  
B=50mA  
Package explain:X=TO-3PX  
Voltage:60=600V 80=800V

## Ordering information

| Part number | Package         | Marking    | Packing | Quantity |
|-------------|-----------------|------------|---------|----------|
| AIS40C60XB  | TO-3PX isolated | AIS40C60XB | Tube    | 30pcs    |
| AIS40C80XB  | TO-3PX isolated | AIS40C80XB | Tube    | 30pcs    |

Note:B = Gate Trigger Current Sensitivity and type

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